

## Unit - 3 LASER

Full form - Light Amplification by Stimulated Emission of Radiation.

\* Definition :- LASER is a process by which one can get a strong intense, Monochromatic & Unidirectional and highly coherent beam of light.

\* Application of LASER.

- (i) In medical field.
- (ii) LASER printer, LASER mouse, LASER light.
- (iii) \* In Aircraft (Radar System Based)
- (iv) In material science [LASER Beam machine].

• Interaction of Light with matter :-

Every matter consists of small atoms and atoms consists a central tiny partical (Nucleus) and  $e^-$  revolved around the nucleus in various energy levels (Orbitals).

→ Here we consider two energy level system for LASER  $E_1$  = energy level one also called ground state. and  $E_2$  = energy level two also called excited state.

Excited State  $E_2$  ( $N_2$ )

(Ground State)  $E_1$  ( $N_1$ )

$N_1$  &  $N_2$  = Population density per unit volume (No of atoms)

• There are three basic processes

- (i) Absorption or Stimulated absorption
- (ii) Spontaneous emission
- (iii) Stimulated emission/Induced emission

Lifetime =  $10^{-8}$  sec

## (1) Absorption / Stimulated Absorption :- ( $N_2 \gg N_1$ )

Let us consider two energy levels of ground and excited state for  $h\nu$  an atom. → Suppose if a photon of ( $h\nu$ ) energy

interact with an atom present in the ground states. Then the atom gets Excitation from ground to excited state. This process is called Absorption.

Let,

$R_{12}^{(abs)}$  = Rate of absorption from Level - 1 to Level 2

$$R_{12}^{(abs)} \propto N_1 \cdot i_i$$

$$R_{12}^{(abs)} \propto U[V] - i_i$$

by combining both

$$R_{12}^{(abs)} \propto N_1 U[V]$$

$$R_{12}^{(abs)} = B_{12} N_1 U[V]$$

$U[V]$  = Incident energy density

(Density of photons)

$B_{12}$  = Coefficient of

Ginstien's for absorption.

## (2) Spontaneous Emission :-

→ If a photon of energy ( $h\nu$ ) interact with an atom present in the ground state, the atom gets excitation from ground state to excited state. The excited atom does not stay for a long time in excited state due to limited lifetime ( $10^{-8}$  sec) and get de-excited and this process is called Spontaneous emission.

Let

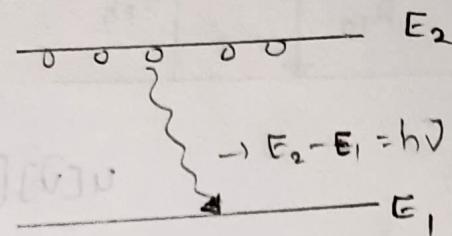
$R_{21} \epsilon \rightarrow$  Rate of spontaneous emission from level 2 to level 1.

$$R_{21} (\text{sp}) \propto N_2$$

$$\boxed{R_{21} (\text{sp}) = A_{21} N_2}$$

$A_{21}$  = Einstein's coefficient of spontaneous emission.

— i.e.



### (3) Stimulated emission:-

Consider a Photon of proper energy incident on two energy level system then it may be possible that it interact with an atom lies in excited state and force into jump into lower state. and emit a photon energy. So finally two photons are emitted (Both in same phase and same direction) such type of emission is called stimulated or Induced emission.

Let

$$R_{21} (\text{stimulated}) \propto N_2 \underset{\text{emission}}{\sim}$$

$$R_{21} \propto u [\nu] \underset{\text{— i.e.}}{\sim}$$

$$\boxed{h\nu = E_2 - E_1}$$

$$R_{21} (\text{sti}) \propto N_2 u [\nu]$$

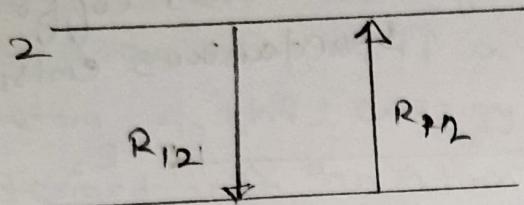
$$R_{21} (\text{sti}) = B_{21} N_2 u [\nu]$$

Here

$B_{21}$  = Coefficient of Einstein's for stimulated emission.

## ★ Relation Between Einstein's coefficient :-

→ In thermal equilibrium rate of Absorption is equal to Rate of emission.



$$R_{12} \text{ (Rate of absorption)} = R_{21} \text{ (Rate of emission)}$$

$$B_{12}N_1U[\nu] = A_{21}N_2 + B_{21}N_2U[\nu]$$

$$U[\nu][N_1B_{12} - B_{21}N_2] = A_{21}N_2$$

$$U[\nu] = \frac{A_{21}N_2}{B_{12}N_1 - B_{21}N_2}$$

$$U[\nu] = \frac{A_{21}N_2}{\left( \frac{B_{12}N_1}{B_{21}N_2} - 1 \right) B_{21}N_2}$$

$$U[\nu] = \frac{A_{21}/B_{21}}{\left[ \frac{B_{12}}{B_{21}} \left( \frac{N_1}{N_2} \right) - 1 \right]}$$

→ i.e.

→ To find  $N_1/N_2$  we use Maxwell Boltzmann statistics. No. of atoms in a given energy state of energy E and at temp T is given by

$$N_i = N_0 e^{-E_i/kT}$$

$$N_1 = N_0 e^{-E_1/kT}$$

$$N_2 = N_0 e^{-E_2/kT}$$

$$\text{So } \frac{N_1}{N_2} = e^{-\frac{1}{kT}(E_1 - E_2)}$$

$$\frac{N_1}{N_2} = e^{+\frac{1}{kT}(E_2 - E_1)}$$

$$\therefore h\nu = E_2 - E_1$$

$$\frac{N_1}{N_2} = e^{\frac{h\nu}{kT}}$$

So by eq .(i)

$$U[\nu] = \frac{A_{21}/B_{21}}{\left[ \frac{B_{12}}{B_{21}} e^{\frac{h\nu}{kT}} - 1 \right]} \quad \text{--- (i)}$$

Note Energy Density  $U[\nu]$  is given by Max Planck.

in black body radiation

$$U[\nu] = \frac{8\pi h\nu^3/c^2}{[e^{\frac{h\nu}{kT}} - 1]} \quad \text{--- (ii)}$$

by comparing eq (i) & (ii)

$$A_{21}/B_{21} = 8\pi h\nu^3/c^2 \quad \& \quad \frac{B_{12}}{B_{21}} = 1$$

$\Rightarrow \boxed{\frac{A_{21}}{B_{21}} \propto \nu^3}$

$$\boxed{B_{12} = B_{21}}$$

At high frequency (in visible region) the probability of spontaneous emission is much greater than stimulated emission.

As the probability of absorption and stimulated emission is always equal.

## Threshold Condition for LASER Operation :-

$$\text{Rate of Absorption} \Rightarrow R_{12}(\text{abs}) = B_{12} N_1 u[\text{v}]$$

$$\text{Rate of Spontaneous emission} \Rightarrow R_{12}(\text{spo. emission}) = A_{21} N_2$$

$$\text{Rate of stimulated emission} \Rightarrow R_{21}(\text{Sto emission}) = B_{21} N_2 u[\text{v}]$$

for LASER action  $\Rightarrow$  Rate of emission is much more greater than rate of absorption (Non-equilibrium process)

$$\frac{R_{21}(\text{emission})}{R_{12}(\text{Absorption})} \gg 1 \Rightarrow \frac{B_{21} N_2 u[\text{v}] + A_{21} N_2}{B_{12} N_1 u[\text{v}]} \gg 1$$

$$\frac{B_{21} N_2}{B_{12} N_1} + \frac{A_{21} N_2}{B_{12} N_1 u[\text{v}]} \gg 1 \quad \text{As we know that } B_{12} = B_{21}$$

$$\frac{N_2}{N_1} \left[ 1 + \frac{A_{21}}{u[\text{v}] B_{12}} \right] \gg 1$$

from this eq.

$$\frac{N_2}{N_1} \gg 1$$

$\boxed{N_2 \gg N_1}$  this condition is also known as population inversion.

Q Calculate the ratio of Population of two energy source of LASER, the transition between which is responsible for emission of Photons of wave length  $6928\text{ \AA}$ , Assume the transition temp. to be  $18^\circ\text{C}$

$$\frac{N_2}{N_1} = \text{Given } \lambda = 6928\text{ \AA} \quad N_2/N_1 = ?$$

$$T = 18 + 273 = 291\text{ K}$$

$$\frac{N_2}{N_1} = e^{(E_2 - E_1)/kT}$$

$$E_2 - E_1 = h\nu = \frac{hc}{\lambda}$$

$$E_2 - E_1 = \frac{6.62 \times 10^{-34} \cdot 3 \times 10^8}{6928 \times 10^{-10}}$$

$$E_2 - E_1 = 2.8 \times 10^{-20}$$

$$\frac{N_2}{N_1} = e^{\frac{2.8 \times 10^{-20}}{1.38 \times 10^{-23} \times 291}}$$

$$\frac{N_2}{N_1} = e^{0.069 \times 10^3}$$

$$\frac{N_2}{N_1} = e^{69} = 8.25 \times 10^{+32} \text{ Any}$$

### Components of a LASER System :-

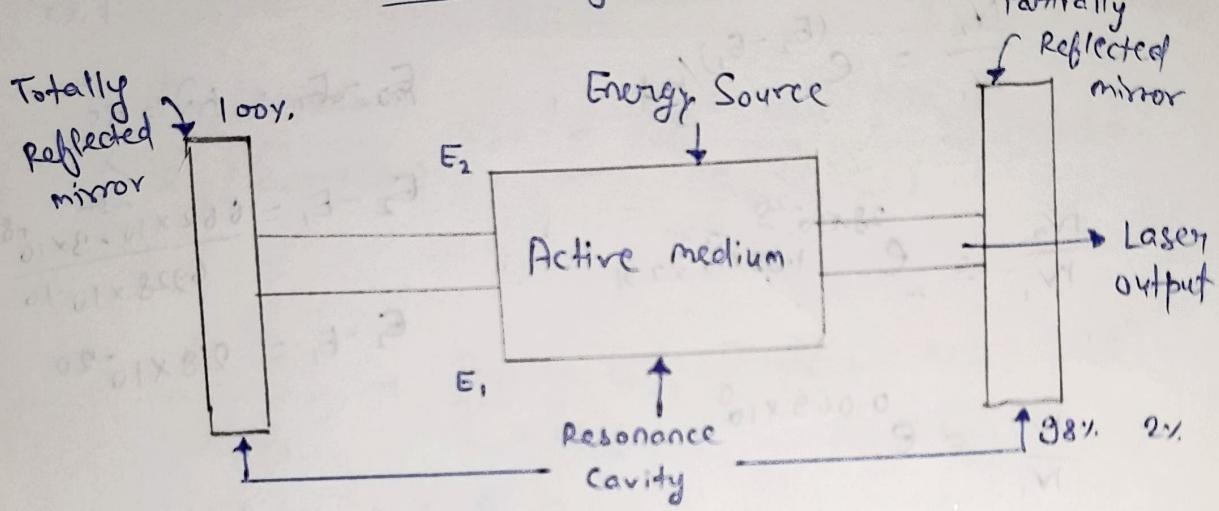
- (1) LASER active medium or Active material.
- (2) Optical Resonator
- (3) Pumping Source (Energy Source)
- (4) Cooling system [He-Ne Sem]

### (1) LASER active medium Active material-

- Active medium in a LASER is a collection of atoms or molecules that generates ~~LASER~~ LASER light.
- LASER medium is also known as active medium or gain medium.

- The active medium is pumped into an excited state which is a higher energy state this is done by supplying energy through an electric current.
- The active medium can be in a solid, liquid and gaseous or plasma state. The method used to introduce energy into the active medium depends on its state.

Block diagram of a laser



## (2) Pumping Source (Energy Source)

The process by which population inversion ( $N_2 \gg N_1$ ) is achieved in a LASER system is called pumping Source

The type of pumping method used depends on nature of Active medium used in LASER System

- for ex- In Solid state LASER such as ruby LASER, we use optical pumping. In Gaseous state such as He-Ne LASER we use electrical pumping,
- Pumping Source is an energy source used to create population inversion ( $N_2 \gg N_1$ )

## Methods of Pumping

(a) Optical Pumping

(b) Electrical Pumping

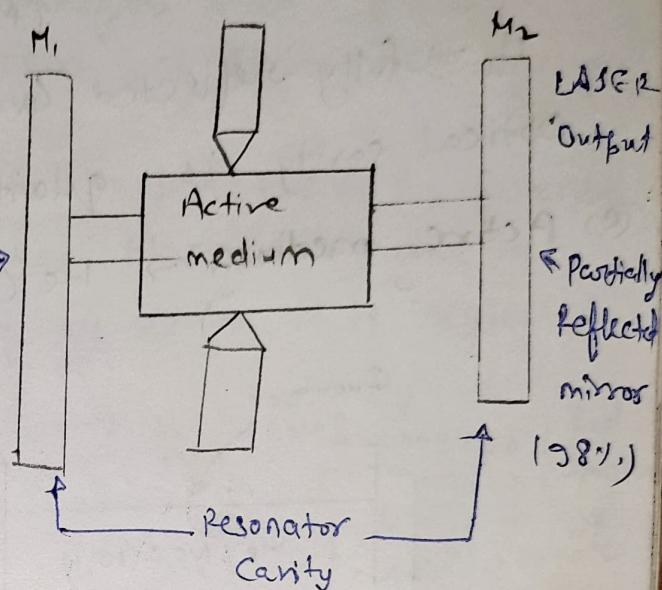
(c) Chemical Pumping

(d) Electron Impact

## (3) Optical Resonators :-

(Resonators Cavity)

→ It is an arrangement of two plane mirrors, One mirror is totally reflected and other is partially reflected.



→ LASER active medium is placed between optical resonators and mirror  $m_2$  is also called output coupler.

## \* He-Ne LASER

### (i) Characteristics of He-Ne LASER

(a) It is a gas LASER

(f) Electrical pumping is required

(b) 4 Level LASER

$E_1$   
 $E_2$  (energy)  
 $E_3$  (level)  
 $E_4$

(g) No External Cooling is required.

(c) active medium

He with Ne ( $10:1$ ) ratio

(d) High efficiency comparatively ruby LASER

(e) Continuous output LASER ( $6328 \text{ Å}$ )

## (ii) Construction of He-Ne LASER

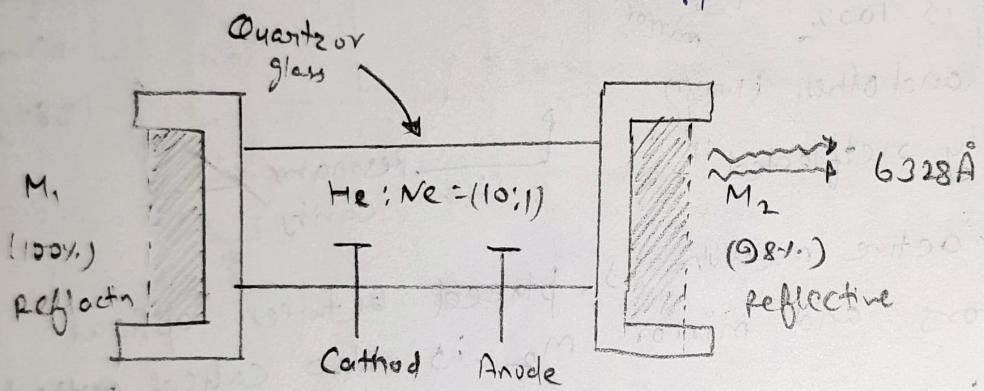
(a) General Parameters  $\rightarrow$  Tube length upto 80cm and diameter 1.5 cm

(b) Optical Cavity/Resonator  $\rightarrow$  It has two mirrors  
(Plane or spherical)

$M_1 \rightarrow$  fully reflected &  $M_2 \rightarrow$  partially reflected.

Optical cavity is quartz or glass cavity.

(c) Active medium  $\rightarrow$  He & Ne gas in the ratio of 10 : 1

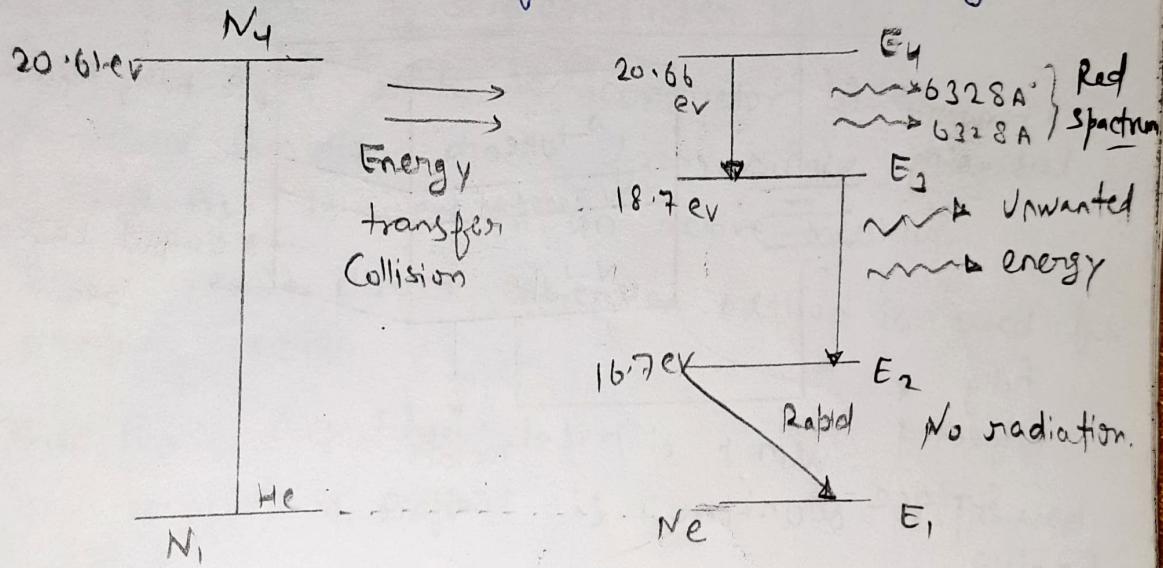


(d) Brewster's window  $\rightarrow$  It is a substrate acting as a polariser used to eliminate unwanted energy, wavelength.

(e) Energy pumping source  $\rightarrow$  Electrical pumping is used as cathode & anode terminals are in gas discharged tube.

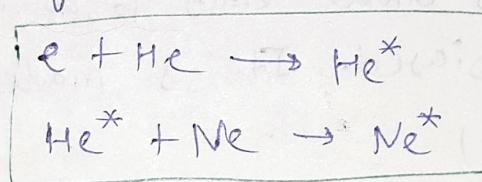
### (iii) Working Principle:- 4 Level LASER Process.

- The electrical discharged accelerators the e<sup>-</sup>s. These electrons collide with Ne atoms and these are raised to N<sub>1</sub> to N<sub>4</sub>. These excited Ne atoms can not deexcite spontaneously rather they collide with Ne atoms and transfer their excited energies through the process of resonance energy transfer.
- Ne atoms are excited to level E<sub>4</sub> to E<sub>3</sub> Reverse energy transfer also takes place, but due to small concentration of Ne atom, it is neglected.



mass of He  $\rightarrow$  4 amu

mass of Ne  $\rightarrow$  20.1 amu (5xHe)



Here  
He\* & Ne\* is  
excited state

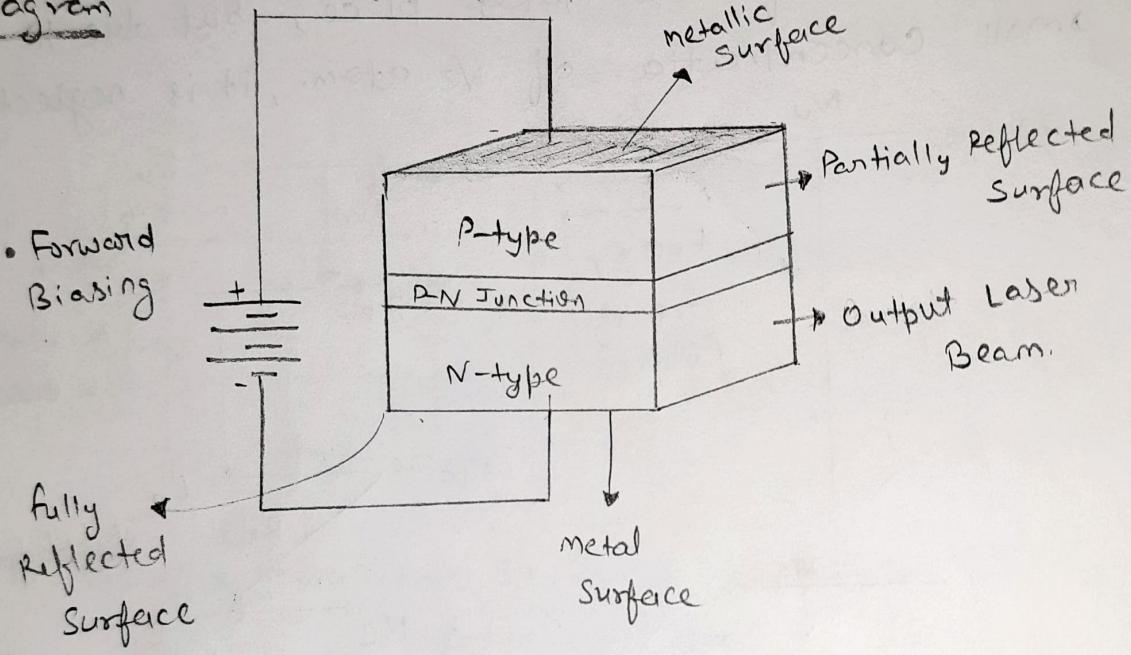
# Semiconductor LASER

(diode)

## Components

- (i) Active medium :- Depletion Region between P-N Junction  
(Thickness -  $0.1\mu\text{m}$ )
- (ii) Pumping Source :- Biasing, External Battery.
- (iii) Resonant Cavity :- P-N Junction acts as a resonant cavity.

## Diagram



- Definition It is a specific fabricated P-N Junction diode. This diode emits laser light when it is forward biased. It is made from Ga-As (gallium-Arsenic)

- Advantage of Semiconductor LASER

1. It has high efficiency (70 to 80%).
2. The small dimensions of semiconductor LASER make it possible to construct quantum amplifier with extremely high sensitivity.
3. From cost point of view this laser is economical.
4. Low Power Consumption.
5. Construction of this type laser is very simple.

- Characteristics of Semiconductor LASER

1. It is a solid state semiconductor LASER.
2. A P-N Junction made from single crystal of (Ga-As) is used as an active medium.
3. The ~~react~~ direct conversion method is used for pumping action.  
this
4. The Power Output from laser is  $\pm$  mW.
5. The Nature of output is continuous or ~~pulsed~~ pulsed
6. Wavelength of output is  $6500 \text{ \AA}$  in the visible Red region.